

ABSTRACT OF THE DISCLOSURE

The present has an object of reducing a wiring resistance caused by the wiring metal such as bonding wire, and self-inductance, in a semiconductor device for large power, such as IGBT module. Therefore, the invention has at least three or more power terminals superimposed on each other, wherein at least one semiconductor chip is connected electrically in a way to be sandwiched between predetermined two power terminals among the power terminals. A power terminal on one end among the aforementioned superposed power terminals and a power terminal on the other end among the superposed power terminals can be led out in the same direction, for example.

2025 RELEASE UNDER E.O. 14176